

	Hits	Search Text	DBs
7	36	(((bit near6 line near6 contact) or (bit\$3line near6 contact)) same DRAM) and ((substrate or wafer or workpiece) same ((dielectric or BPSG) near26 (deposit\$4 or layer or coat\$4 or film or form\$3)) same (photoresist or resist or polyimide or (silicon near6 nitride)) same (etch\$4 or RIE)) and ((photoresist or resist or photosensitive) same (pattern or mask) same develop\$4 same (expos\$4 or irradiat\$4 or illuminate or photolithograph\$4)) and ((fill\$4 or deposit\$4 or coat\$4) same (window or opening or (bit\$3line near6 contact near4 window) or (aspect near6 ratio) or (contact near9 hole)) same (conductive or metal\$4 or polysilicon or polySi or tungsten or ("W" near3 plug)) same (planarization or planari\$5 or CMP))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
8	0	(((bit near6 line near6 contact) or (bit near12 contact) or (bit\$3line near6 contact)) same DRAM) and ((substrate or wafer or workpiece) same ((dielectric or BPSG) near26 (deposit\$4 or layer or coat\$4 or film or form\$3)) same (photoresist or resist or polyimide or (silicon near6 nitride) or (hard near9 mask)) same (etch\$4 or RIE)) and ((fill\$4 or deposit\$4 or coat\$4) same (window or opening or (bit\$3line near6 contact near4 window) or (aspect near6 ratio) or (contact near9 hole)) same (conductive or metal\$4 or polysilicon or polySi or tungsten or ("W" near3 plug)) same (planarization or planari\$5 or CMP)) and ((planariz\$6 or CMP) near36 (IPO or dielectric or BPSG or Si\$2N) near29 (gate near9 electrode) near16 (expos\$4 or reveal\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
9	28	(((bit near6 line near6 contact) or (bit near12 contact) or (bit\$3line near6 contact)) same DRAM) and ((substrate or wafer or workpiece) same ((dielectric or BPSG) near26 (deposit\$4 or layer or coat\$4 or film or form\$3)) same (photoresist or resist or polyimide or (silicon near6 nitride) or (hard near9 mask)) same (etch\$4 or RIE)) and ((fill\$4 or deposit\$4 or coat\$4) same (window or opening or (bit\$3line near6 contact near4 window) or (aspect near6 ratio) or (contact near9 hole)) same (conductive or metal\$4 or polysilicon or polySi or tungsten or ("W" near3 plug)) same (planarization or planari\$5 or CMP)) and ((planariz\$6 or CMP) same (IPO or dielectric or BPSG or Si\$2N) same (gate near9 electrode) same (expos\$4 or reveal\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB